

-30V P-CHANNEL Power MOSFET

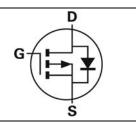
V_{DSS}, -30V

 $R_{DS(ON)}$, $14m\Omega$ (max.) @ VGS=-10V $R_{DS(ON)}$, $24m\Omega$ (max.) @ VGS=-4.5V

 I_D , -9A

SOP-8





Description

The SGP3011S uses advanced trench technology MOSFETs to provide excellent R_{DS(ON)} and low gate charge.

The complementary Power MOSFETs may be used in H-bridge, Inverters and other applications.

Features

- Low On-Resistance
- Low Input Capacitance
- Low Miller Charge
- Low Input / Output Leakage
- · Pb-free lead plating; RoHS compliant

Applications

- Motor / Body Load Control
- Automotive Systems
- Load Switch

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGP3011S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	±20	V
Drain Current-Continuous	T _A =25°C		-9	А
Drain Current-Continuous	T _A =70°C	lo lo	-6	А
Drain Current-Pulsed Note 1		I _{DM}	-45	А
Avalanche Current		las	-50	А
Avalanche Energy, L=0.1mH		E _{AS}	125	mJ
Maximum Davier Dissipation	T _A =25°C	D	1.7	W
Maximum Power Dissipation	T _A =70°C	P _D	0.7	W
Operating Junction Temperature Rang	e	T _J T _{STG}	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 2	R _{θJA}	Steady State	-	-	75	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	24	°C/W

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Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =-250µA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =-250µA	-1	-1.5	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _{DS} =-10A	-	-	14	mΩ
		V _{GS} =-4.5V, I _{DS} =-5A	-	-	24	

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	2170	-	
Output Capacitance	Coss	V _{DS} =-15V, V _{GS} =0V, f=1MHz	-	303	-	pF
Reverse Transfer Capacitance	Crss		-	232	-	
Forward Transconductance	gfs	V _D =-5V, I _D =-9A	-	29	-	S

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	$T_{d(on)}$		-	8	-	
Rise Time	tr	V_{DD} =-15V, V_{GS} =-10V, R_{G} =3.3 Ω , I_{D} =-	-	73.7	-]
Turn-Off Delay Time	$T_{d(off)}$	9A	-	61.8	-	ns
Fall Time	t _f]	-	24.4	-	
Total Gate Charge at -4.5V	Qg	V 45V V 45V	-	21	-	
Gate to Source Gate Charge	Qgs	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-9A	-	8.5	-	nC
Gate to Drain "Miller" Charge	Q_{gd}	1 ID3A	-	7.1	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-9A	-	-	-1.2	V
Continuous Source Current	ls	\/ =\/ =0\/ Fares Current	-	-	-49	Α
Pulsed Source Current	I _{SM}	- V _G =V _D =0V, Force Current	-	-	-150	Α
Body Diode Reverse Recovery Time	trr	V _{DD} =-15V, I _F =-9A, di/dt=100A/μs	-	18	-	ns
Body Diode Reverse Recovery Charge	Qrr	V _{DD} =-15V, I _F =-9A, di/dt=100A/μs	-	8	-	nC

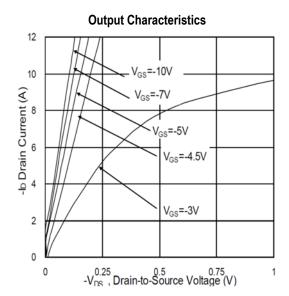
Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BJA} is determined by the user's board design. R_{BJA} shown below for single device operation on FR-4 in still air.

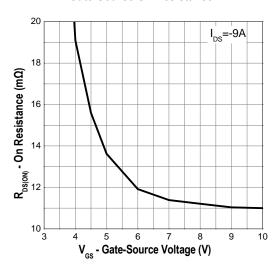


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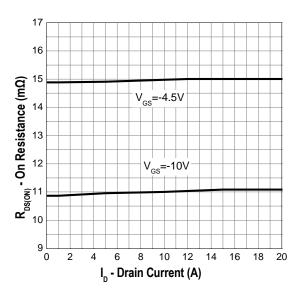
Typical Operating Characteristics



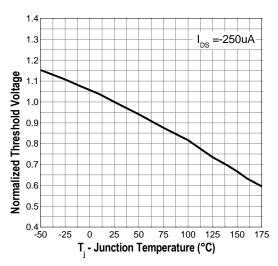
Gate-Source On Resistance



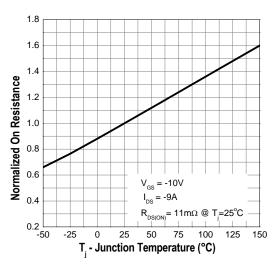
Drain-Source On Resistance



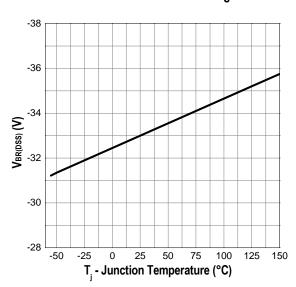
Gate Threshold Voltage



Drain-Source On Resistance



Drain-source Breakdown Voltage

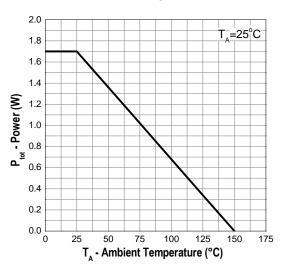




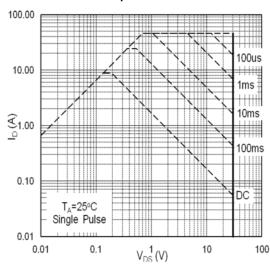
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Typical Operating Characteristics (Cont.)

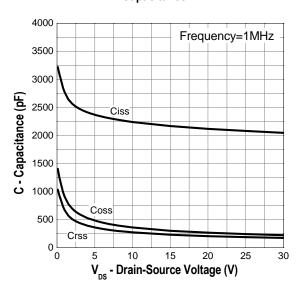
Power Dissipation



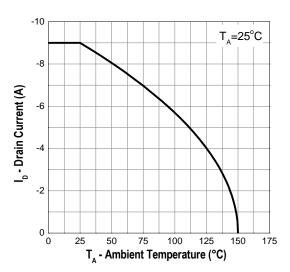
Safe Operation Area



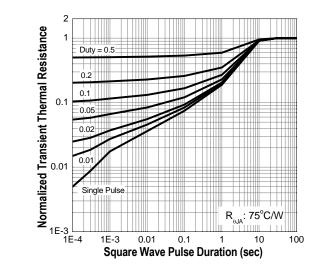
Capacitance



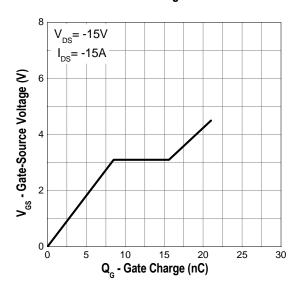
Drain Current



Transient Thermal Impedance



Gate Charge





SGP3011S
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Marking Information

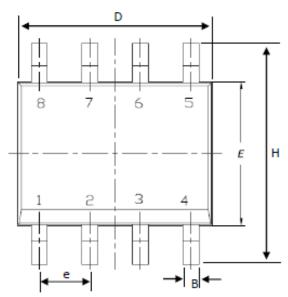
SOP-8 (S)	Marking Rule
Laser Marking	Line 1 : Device
	SGP3011S
	Line 2 : Date Code
SGP3011S	YYMMXXX
YYMMXXX	YY: Year Code
	MM: Month Code
	XXX : Serial Number



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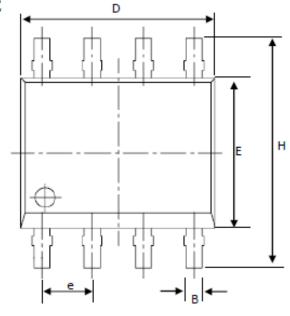
Package of Dimension

G-TYPE



Symbol	Min	Nor	Max
Α	1.35	1.55	1.75
A1	0.10	0.18	0.25
В	0.31	0.41	0.51
С	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27	1.27	1.27
Н	5.80	6.00	6.20
Ĺ	0.40	0.84	1.27
α	0.00	4.00	8.00

B-TYPE





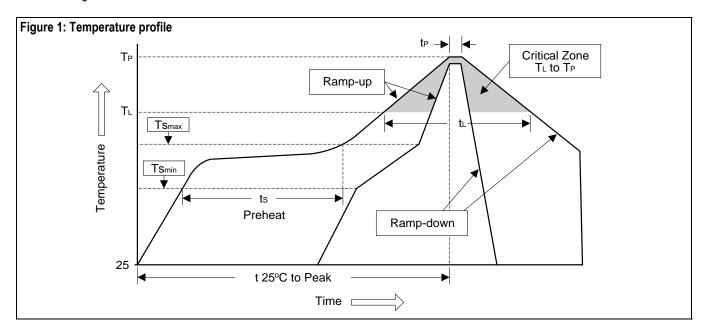
- 1. All dimension are in millimeters.
- 2. Dimension does not include burrs and mold flash/protrusions.



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Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t₂)	10 to 50 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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